

2SK3396

Silicon N-Channel Junction FET

For impedance conversion in low frequency

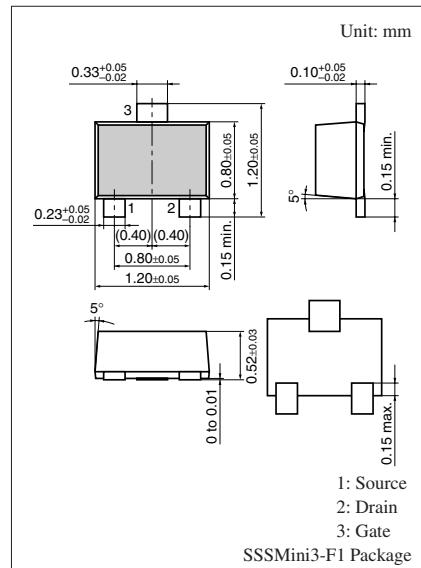
For infrared sensor

■ Features

- Low gate-source cutoff current I_{GSS}
- Small capacitance of short-circuit forward transfer capacitance (common source) C_{iss} , short-circuit output capacitance (common source) C_{oss} , reverse transfer capacitance (common source) C_{rss}

■ Absolute Maximum Ratings $T_a = 25^\circ\text{C}$

Parameter	Symbol	Rating	Unit
Gate-drain voltage (Source open)	V_{GDO}	-40	V
Gate-source voltage (Drain open)	V_{GSO}	-40	V
Gate current	I_G	10	mA
Drain current	I_D	1	mA
Power dissipation	P_D	100	mW
Channel temperature	T_{ch}	125	°C
Storage temperature	T_{stg}	-55 to +125	°C

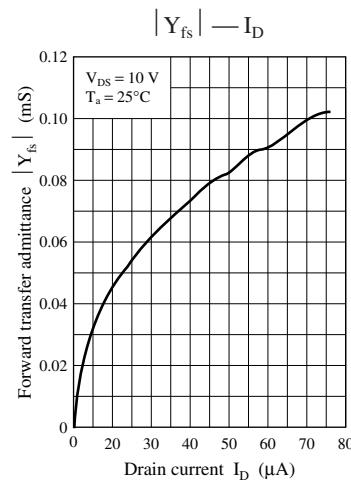
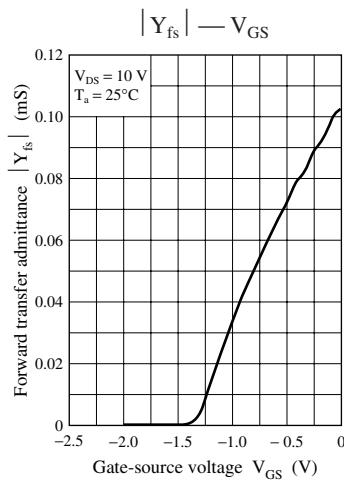
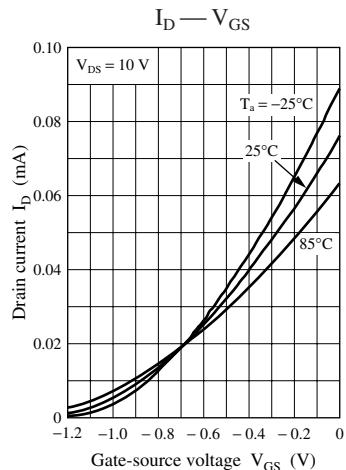
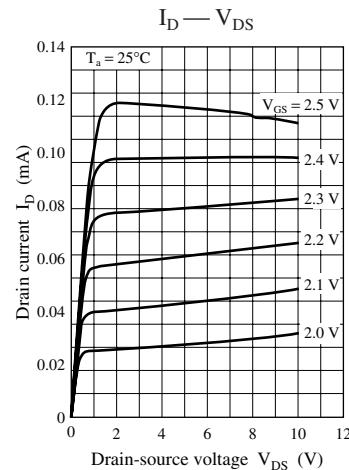
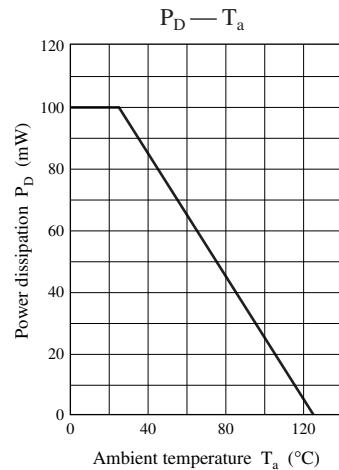


Marking Symbol: EB

■ Electrical Characteristics $T_a = 25^\circ\text{C} \pm 3^\circ\text{C}$

Parameter	Symbol	Conditions	Min	Typ	Max	Unit
Gate-drain reverse voltage	V_{GDS}	$I_G = -10 \mu\text{A}$, $V_{DS} = 0$	-40			V
Drain-source cutoff current	I_{DSS}	$V_{DS} = 10 \text{ V}$, $V_{GS} = 0$	30		200	μA
Gate-source cutoff current	I_{GSS}	$V_{GS} = -20 \text{ V}$, $V_{DS} = 0$			-0.5	nA
Forward transfer admittance	$ Y_{fs} $	$V_{DS} = 10 \text{ V}$, $V_{GS} = 0$, $f = 1 \text{ kHz}$	0.05			mS
Gate-source cutoff voltage	V_{GSC}	$V_{DS} = 10 \text{ V}$, $I_D = 1 \mu\text{A}$		-1.3	-3.0	V
Short-circuit forward transfer capacitance (Common source)	C_{iss}	$V_{DS} = 10 \text{ V}$, $V_{GS} = 0$, $f = 1 \text{ MHz}$		1.0		pF
Short-circuit output capacitance (Common source)	C_{oss}	$V_{DS} = 10 \text{ V}$, $V_{GS} = 0$, $f = 1 \text{ MHz}$		0.4		pF
Reverse transfer capacitance (Common source)	C_{rss}	$V_{DS} = 10 \text{ V}$, $V_{GS} = 0$, $f = 1 \text{ MHz}$		0.4		pF

Note) Measuring methods are based on JAPANESE INDUSTRIAL STANDARD JIS C 7030 measuring methods for transistors.



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